

## Product Summary

Device	BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> MAX T <sub>A</sub> = +25°C
Q1 N-Channel	20V	25mΩ @ V <sub>GS</sub> = 4.5V	6.0A
		35mΩ @ V <sub>GS</sub> = 2.5V	5.1A
Q2 P-Channel	-20V	75mΩ @ V <sub>GS</sub> = -4.5V	-3.5A
		140mΩ @ V <sub>GS</sub> = -2.5V	-2.5A

## Features

- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Maximum Height
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**  
<https://www.diodes.com/quality/product-definitions/>

## Description and Applications

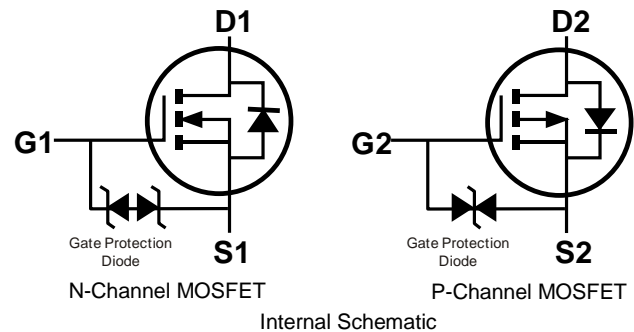
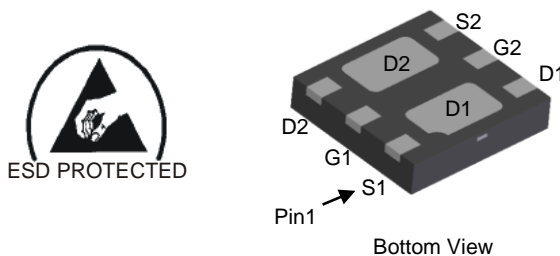
This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- Load Switch
- Power Management Functions
- Portable Power Adaptors

## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e4)**
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type B)



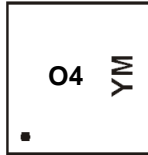
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2025UFDB-7	U-DFN2020-6 (Type B)	3000/Tape & Reel
DMC2025UFDB-13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information

Site 1

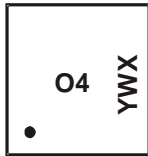


O4 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

<b>Year</b>	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	E	...	H	I	J	K	L	M	N	O	P	R
<b>Month</b>	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
<b>Code</b>	1	2	3	4	5	6	7	8	9	O	N	D

Site 2



O4 = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

<b>Year</b>	2017	...	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
<b>Code</b>	7	...	0	1	2	3	4	5	6	7	8	9
<b>Week</b>	1-26				27-52				53			
<b>Code</b>	A-Z				a-z				z			
<b>Internal Code</b>	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
<b>Code</b>	T	U	V	W	X	Y	Z					

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 N-CHANNEL	Q2 P-CHANNEL	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±10	±8	V
Continuous Drain Current (Note 6) N-Channel: V <sub>GS</sub> = 4.5V P-Channel: V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	6.0	-3.5	A
		T <sub>A</sub> = +70°C		4.8	-2.8	
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	2	-1.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	20	-10	A
Avalanche Current (L = 0.1mH) (Note 7)			I <sub>AS</sub>	8	-13	A
Avalanche Energy (L = 0.1mH) (Note 7)			E <sub>AS</sub>	8	8.5	mJ

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C P <sub>D</sub>	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State R <sub>θJA</sub>	178	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C P <sub>D</sub>	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State R <sub>θJA</sub>	92	°C/W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	30	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics Q1 N-CHANNEL** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	25	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A
		—	—	35		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	486	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	92	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	77	—		
Gate Resistance	R <sub>g</sub>	—	3.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	5.9	—	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.5A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	12.3	—		
Gate-Source Charge	Q <sub>gs</sub>	—	0.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.4	—	ns	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>g</sub> = 6Ω, R <sub>L</sub> = 10Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>r</sub>	—	5.4	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	17.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	9.3	—		
Reverse Recovery Time	t <sub>RR</sub>	—	7.7	—	ns	I <sub>F</sub> = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>R</sub>	—	1.5	—	nC	I <sub>F</sub> = 1A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

**Electrical Characteristics Q2 P-CHANNEL** (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.35	—	-1.4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	75	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.9A
		—	—	140		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.3A
Diode Forward Voltage	V <sub>SD</sub>	—	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.0A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	642	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	98	—	pF	
Reverse Transfer Capacitance	C <sub>riss</sub>	—	87	—	pF	
Gate Resistance	R <sub>g</sub>	—	26.5	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Q <sub>g</sub>	—	8.8	—	nC	V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.7A
Total Gate Charge (V <sub>GS</sub> = -8V)		—	15	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	2.9	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.5	—	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 3.3Ω, R <sub>g</sub> = 1Ω
Turn-On Rise Time	t <sub>R</sub>	—	22.6	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	34.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	34.3	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	13	—	ns	I <sub>S</sub> = -3.0A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	3.3	—	nC	I <sub>S</sub> = -3.0A, dI/dt = 100A/μs

Notes: 8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

**Typical Characteristics - N-CHANNEL**

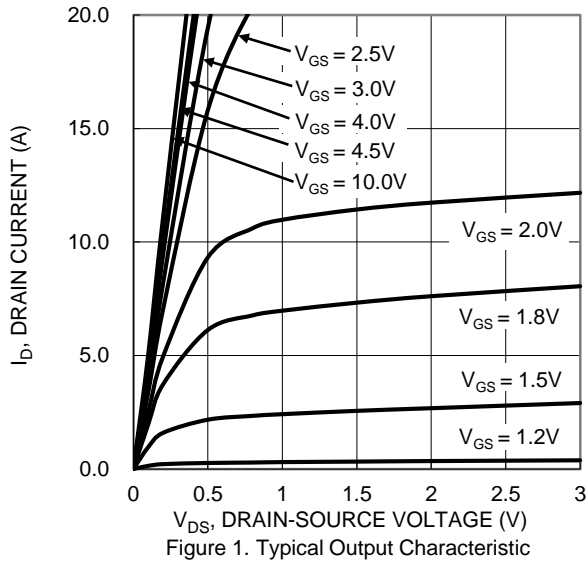


Figure 1. Typical Output Characteristic

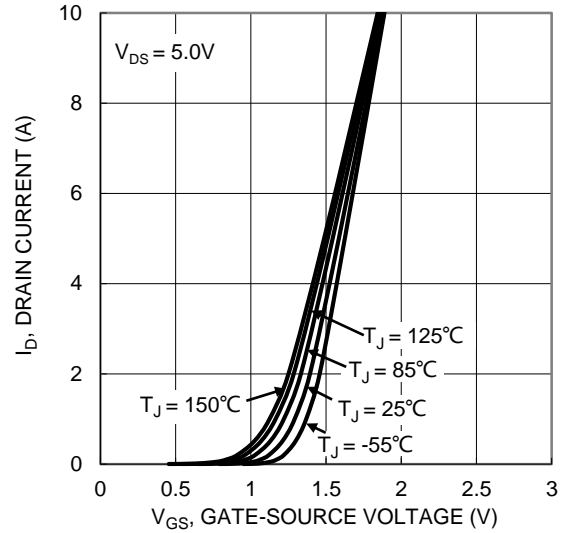


Figure 2. Typical Transfer Characteristic

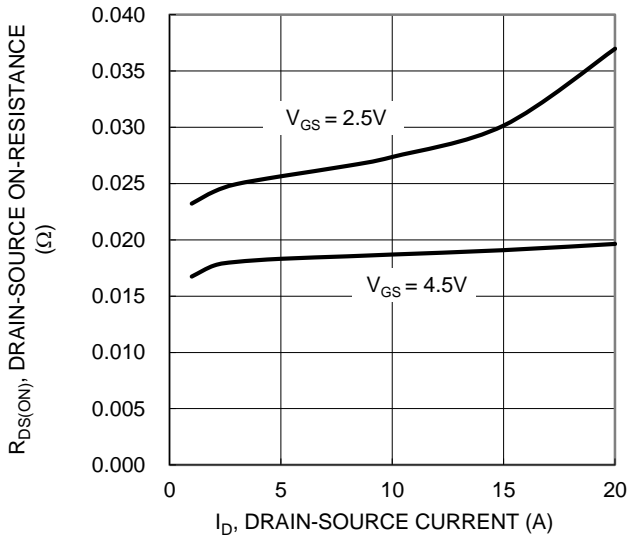


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

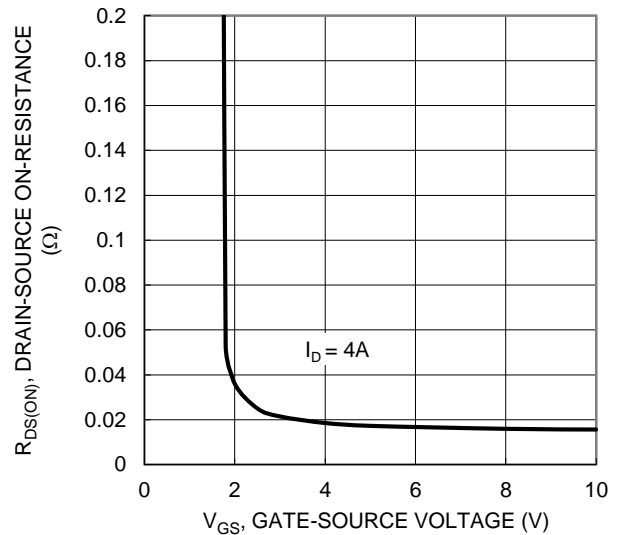


Figure 4. Typical Transfer Characteristic

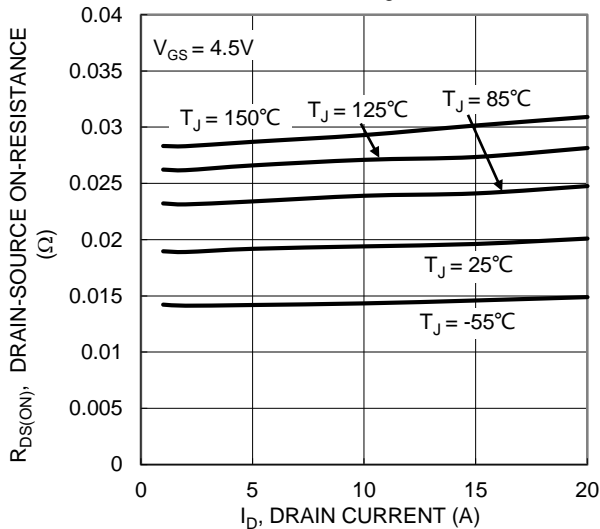


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

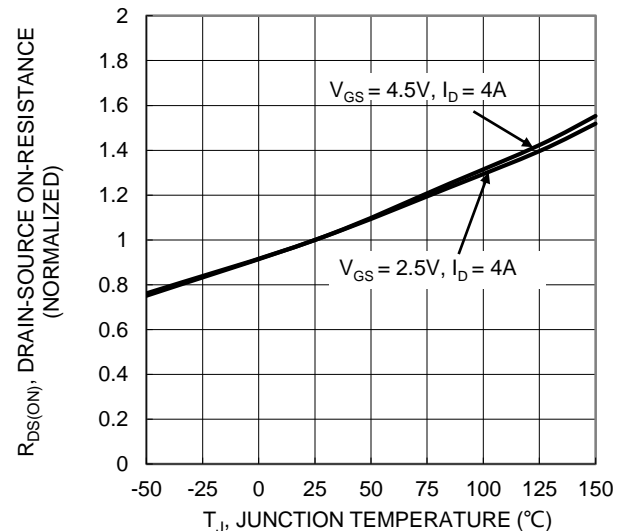


Figure 6. On-Resistance Variation with Temperature

**Typical Characteristics - N-CHANNEL** (continued)

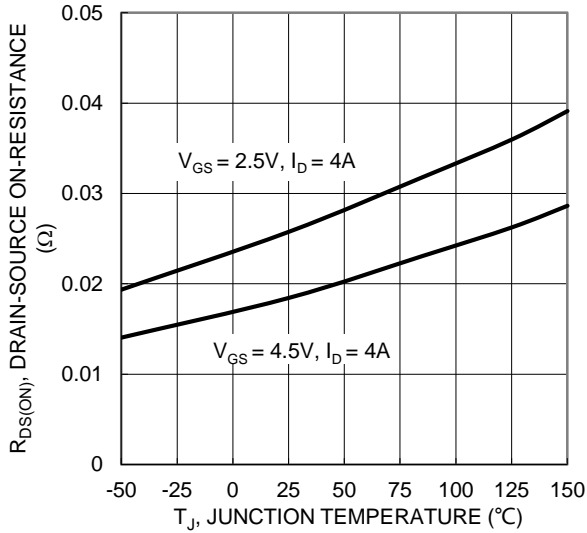


Figure 7. On-Resistance Variation with Temperature

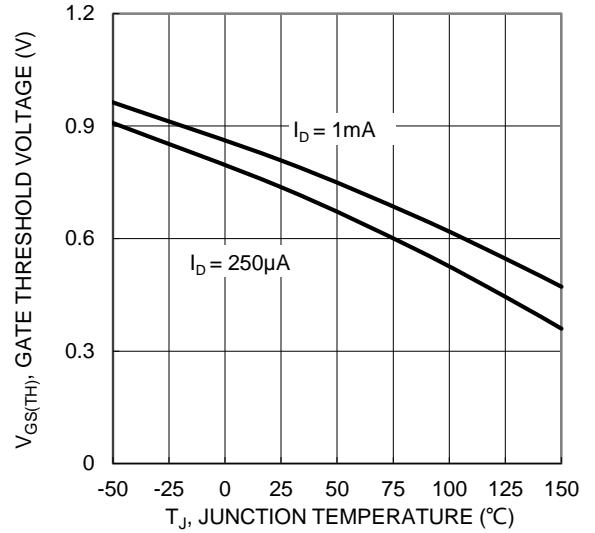


Figure 8. Gate Threshold Variation vs. Junction Temperature

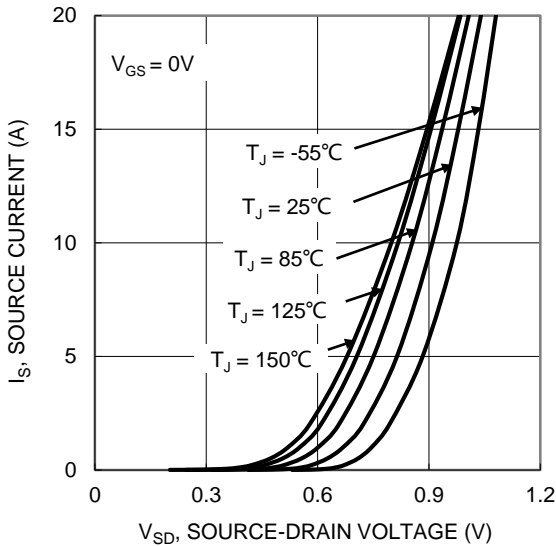


Figure 9. Diode Forward Voltage vs. Current

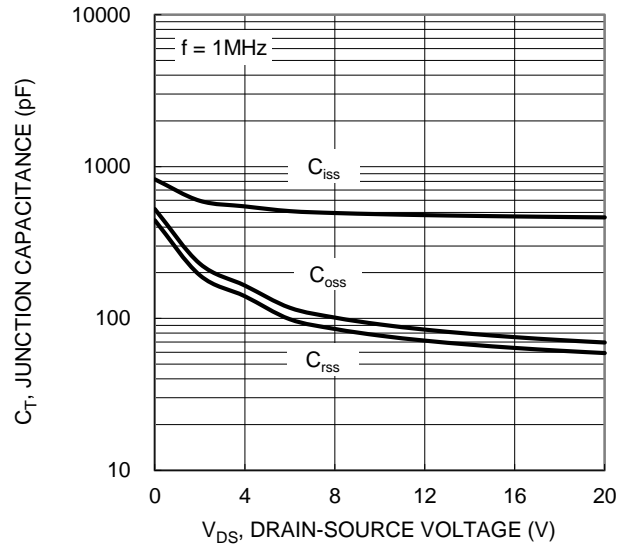


Figure 10. Typical Junction Capacitance

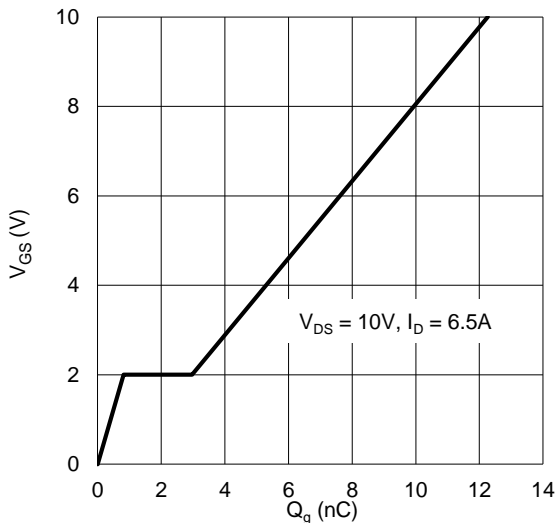


Figure 11. Gate Charge

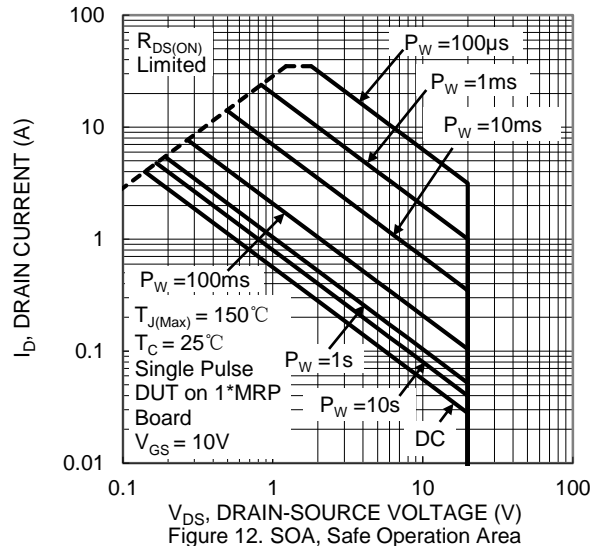


Figure 12. SOA, Safe Operation Area

**Typical Characteristics - P-CHANNEL**

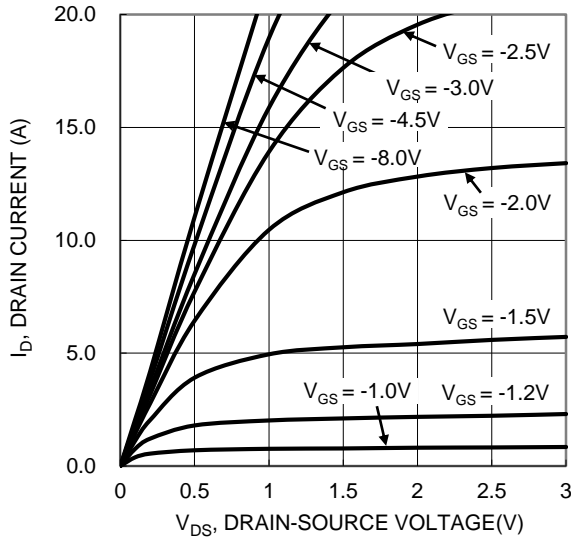


Figure 13. Typical Output Characteristic

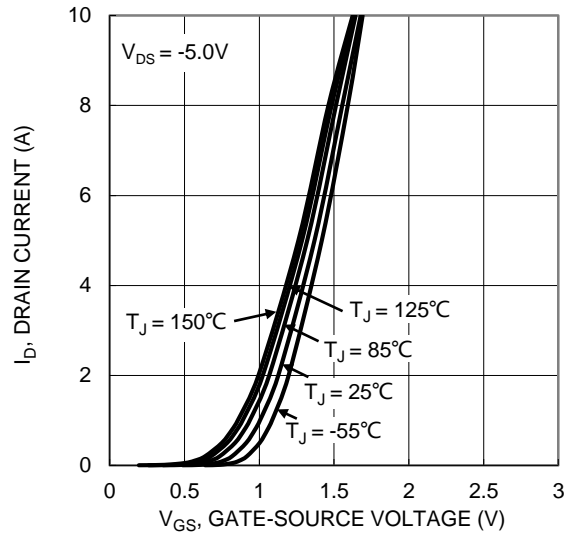


Figure 14. Typical Transfer Characteristic

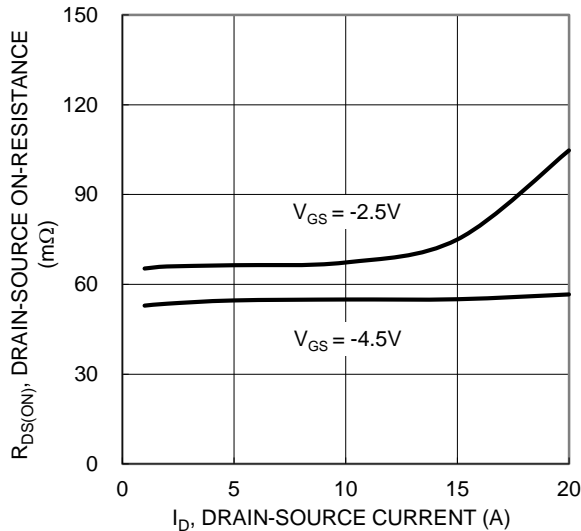


Figure 15. Typical On-Resistance vs. Drain Current and Gate Voltage

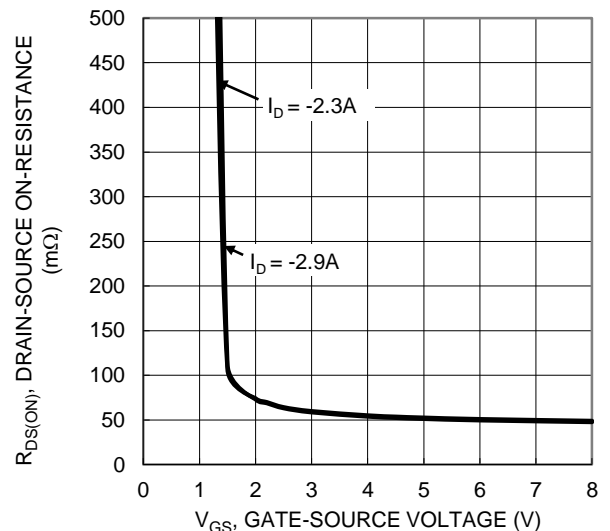


Figure 16. Typical Transfer Characteristic

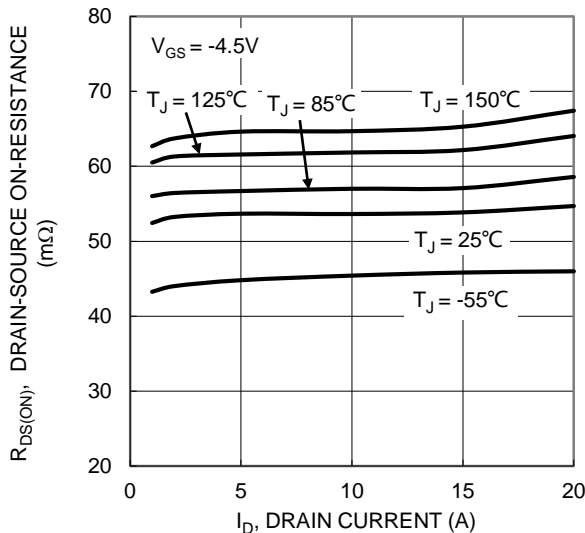


Figure 17. Typical On-Resistance vs. Drain Current and Temperature

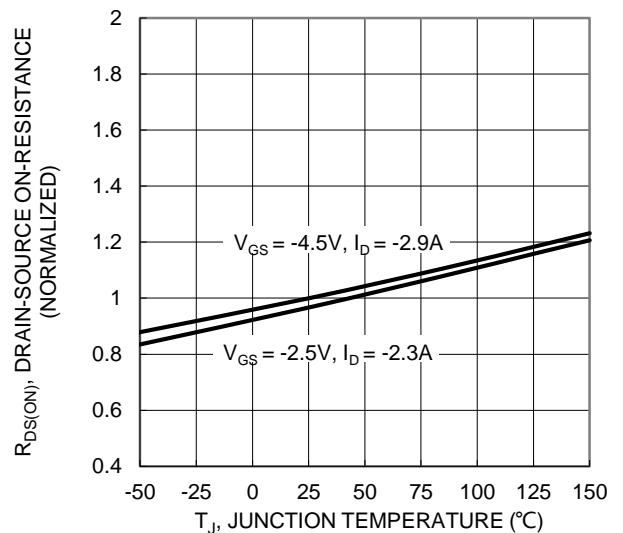


Figure 18. On-Resistance Variation with Temperature

**Typical Characteristics - P-CHANNEL** (continued)

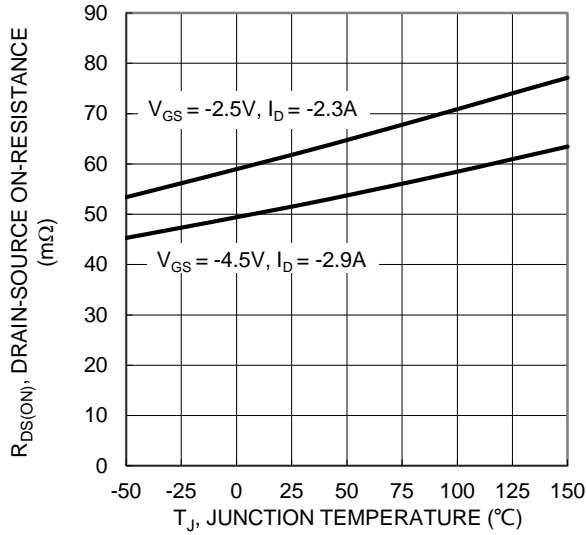


Figure 19. On-Resistance Variation with Temperature

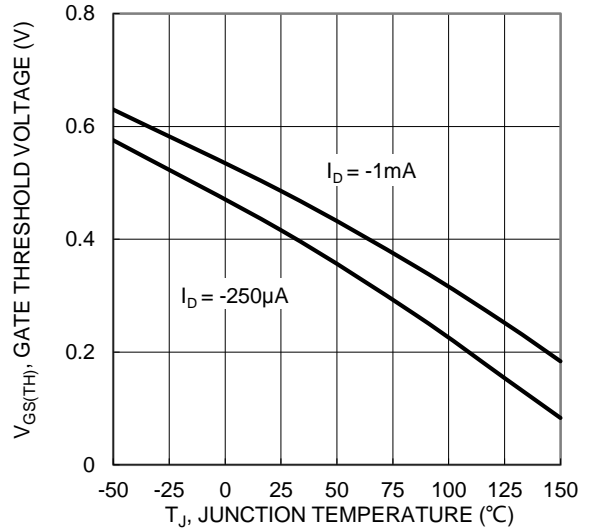


Figure 20. Gate Threshold Variation vs. Junction Temperature

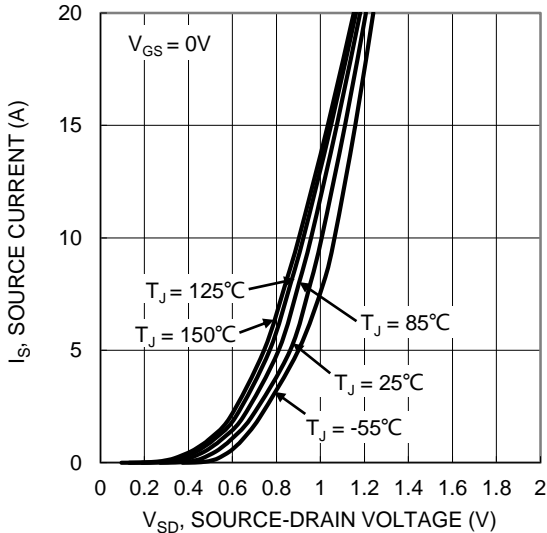


Figure 21. Diode Forward Voltage vs. Current

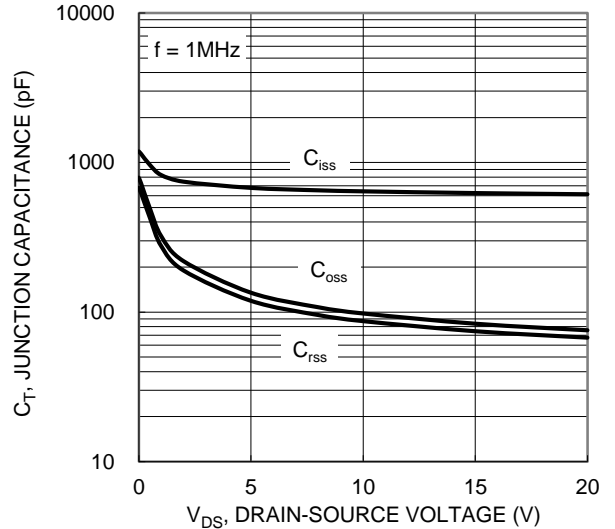


Figure 22. Typical Junction Capacitance

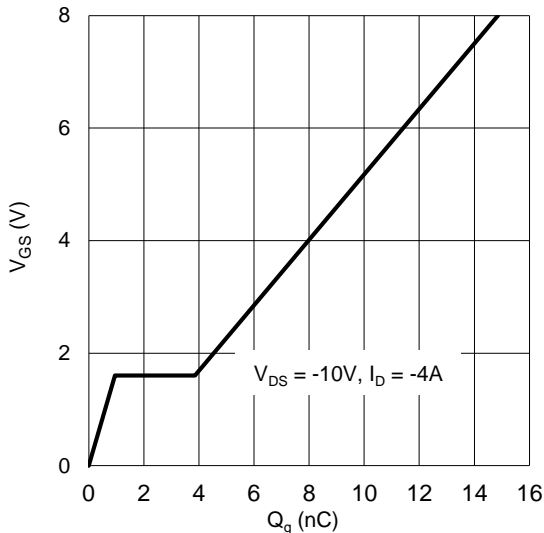


Figure 23. Gate Charge

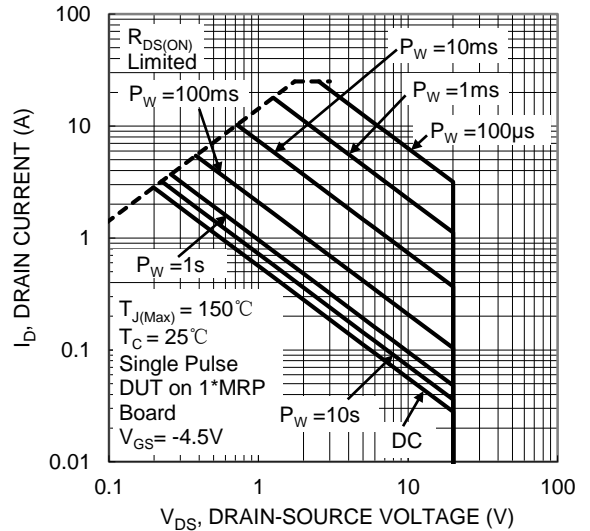


Figure 24. SOA, Safe Operation Area

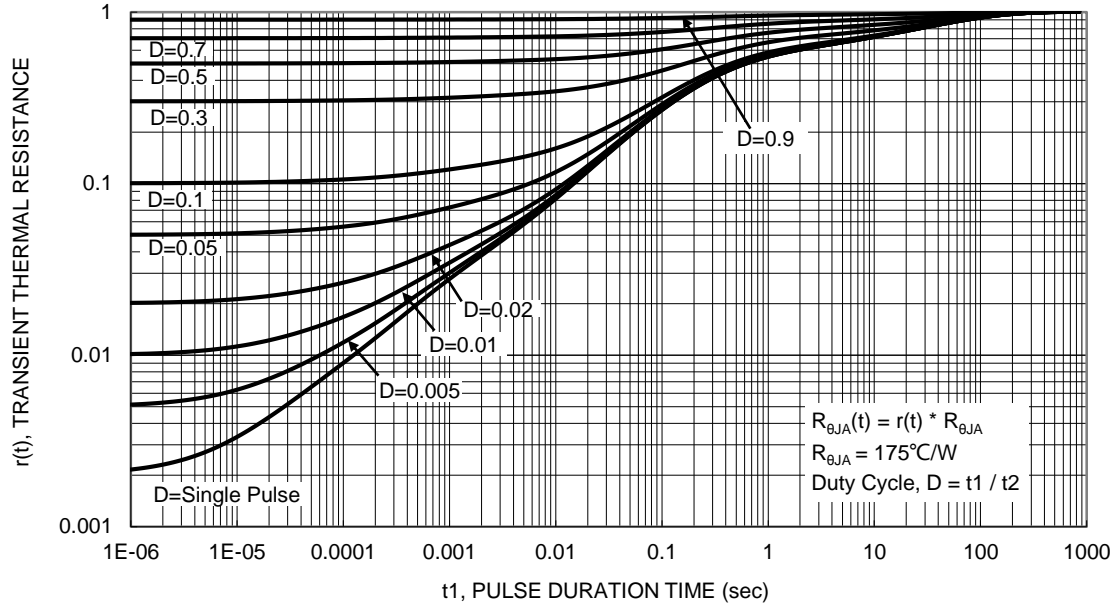
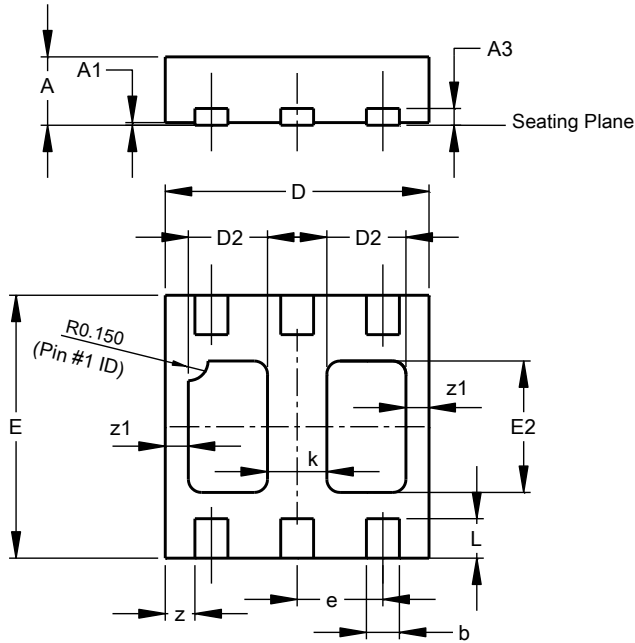


Figure 25. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)

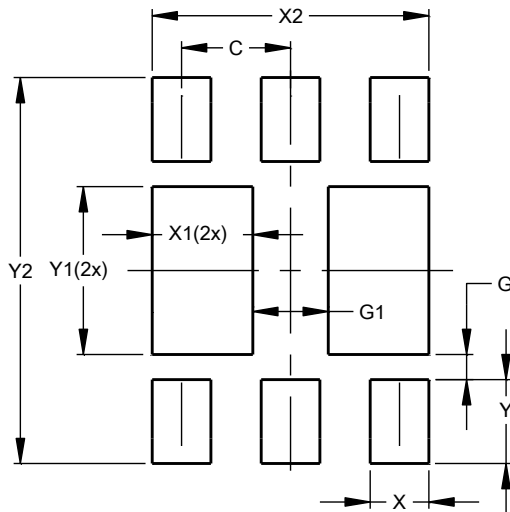


U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	—	—	0.45
L	0.25	0.35	0.30
z	—	—	0.225
z1	—	—	0.175
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type B)



Dimensions	Value (in mm)
C	0.650
G	0.150
G1	0.450
X	0.350
X1	0.600
X2	1.650
Y	0.500
Y1	1.000
Y2	2.300

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A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or
2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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